

Vishay Siliconix

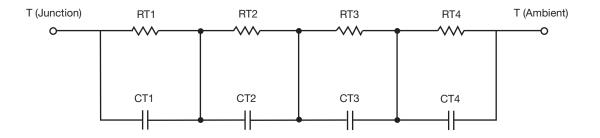
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	-C VALUES FOR TANK CONFIGURATION					
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	n/a	194.0706m	n/a			
RT2	n/a	22.7574m	n/a			
RT3	n/a	24.9656m	n/a			
RT4	n/a	8.6654m	n/a			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	n/a	1.3650	n/a			
CT2	n/a	407.4192m	n/a			
CT3	n/a	31.4272m	n/a			
CT4	n/a	36.6621m	n/a			

Note

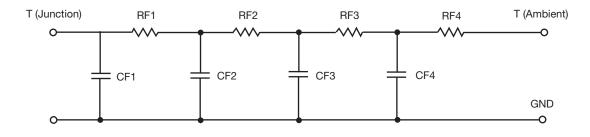
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	n/a	11.7805m	n/a		
RF2	n/a	33.0352m	n/a		
RF3	n/a	46.1976m	n/a		
RF4	n/a	160.0208m	n/a		
	THERMAL CAPAC	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	18.7617m	n/a		
CF2	n/a	1.8818m	n/a		
CF3	n/a	670.7442m	n/a		
CF4	n/a	823.6124m	n/a		

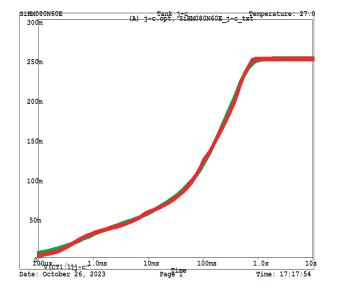
Note

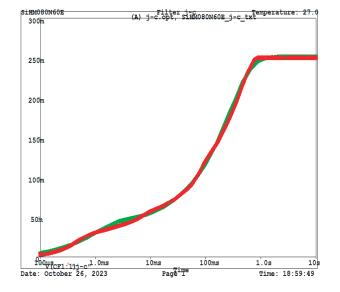
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